

Publication list of Andrey Muraviev  
(also under name spelling: A.V.Muravjov)

1. Jae Kyu Choi, Vladimir Mitin, Rahul Ramaswamy, Victor A. Pogrebnyak, Mehdi P. Pakmehr, Andrey Muravjov, Michael S. Shur, John Gill, Imran Mehdi, Boris S. Karasik, and Andrei V. Sergeev, THz Hot-Electron Micro-Bolometer Based on Low-Mobility 2-DEG in GaN Heterostructure, *IEEE Sensors Journal*, Vol. 13, 1, p.80-88 (January, 2013)
2. A.V. Muravjov, D.B. Veksler, V.V. Popov, O.V. Polischuk, N. Pala, X. Hu, R. Gaska, H. Saxena, R.E. Peale, M.S. Shur, «Temperature dependence of plasmonic terahertz absorption in grating-gate GaN HEMT structures», *APL* 96, 042105 (2010)
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